

AMENDMENTS TO THE CLAIMS

1. (Currently Amended) A method of fabricating a capacitor for a semiconductor device, comprising the steps of:
- a) forming a sacrificial layer in the height of the capacitor on ~~the~~ substrate, ~~so that wherein~~ an etch rate of an upper portion of the sacrificial layer is ~~becomes~~ lower if it's than that of a lower portion of the sacrificial layer, wherein the sacrificial layer is a TEOS layer ~~height becomes higher~~;
 - b) forming a trench by selectively eliminating the sacrificiale layer ~~in manner of~~ by a wet etch process;
 - c) forming a bottom electrode in the trench;
 - d) eliminating the sacrificial layer;
 - e) forming a dielectric thin film on the bottom electrode; and
 - f) forming the top electrode on the dielectric thin film.

Claim 2 (Cancelled)

3. (Currently Amended) The method of fabricating the capacitor as recited in claim 12, wherein the sacrificiale layer is formed in response to a RF power, an O₂ flow, and a spacing between the substrate and the shower head, and ~~at the upper lower~~ portion of the sacrificiale layer has a higher wet etching rate than ~~at the lower upper~~ portion of the sacrificiale layer does.

4. (Currently Amended) The method of fabricating the capacitor as recited in claim 3, wherein the sacrificiale layer is deposited in thickness ranging from about 10000 Å to about 25000 Å.